BRS: 32with 33
Pending
Active
L1: (1) 10/718310
L2: (6) 5519236.pn. "20020127803" "20020127786"
L3: (1342) (semiconductor active) adj (strip$4 web)
L4: (17333) second adj2 well
L5: (554) (257/302).CCLS.
L6: (10) 4 and 5
L7: (17854) first adj2 well
L8: (73343) "same" near2 (conduct$4 impurity dop$4)
L9: (4658) 4 with 7
L10: (48) 9 with 8
L11: (45548) (wordline "WL" (word near (read$3 writ$3)))
L12: (3216814) contact
L13: (0) 10 with 11
L14: (5090) deep adj trench
L15: (715) buried adj strap
L16: (180) 14 near9 15
L17: (3149775) identical similar$2
L18: (5) (17 "same") with 16
L19: (1) 09/607217
L20: (20) 2 6 18
Failed
Saved
(1) 09/948877
(1728) "KONINKLIJKE PHILIPS"

Browse   Queue   Clear

DBs: USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   Plurals

Default operator: OR   Highlight all hit terms initially

2 6 18

Aug 2024

#	+	Inventor	Document I	Issue	P	Title	Current	Current XR	Retrieval	S	C	F	1	2	3	Image Doc.	P
1			Bostelmann,	US 6344390	2002.0	2	Methods of forming the buried strap and its q	438/249	257/E21.65		✓			✓				US 634439	
2			Kowalski, Be	US 2004010	2004.0	9	Transistor array and semiconductor memory	257/302			✓				✓			US 200401	
3			Losee, Becky	US 2002019	2002.1	1	Method for etching silicon trenches	438/709	257/302;		✓							US 200201	
4			Schlosser, Til	US 2002012	2002.0	1	Method for producing a memory cell for a se	438/258	257/E21.65		✓							US 200201	
5			Hofmann, Fra	US 2002012	2002.0	1	Method for producing a cell of a semiconduct	438/243	257/E21.65		✓							US 200201	
6			Kim, Ho-Hyun	US 2002008	2002.0	1	MOS control diode and method for manufact	257/135	257/242;		✓							US 200200	
7			Wu, Xiaoju et	US 2002007	2002.0	1	Electronic circuit with electrical hole isolato	257/302	257/E21.37		✓							US 200200	
8			Hsu, Louis L.	US 2002007	2002.0	1	Structure and method for creating vertical c	257/302	257/E23.14		✓							US 200200	
9			Schroeder, H	US 6747303	2004.0	1	CHARGE DETECTOR SEMICONDUCTOR CO	257/296	257/297;		✓							US 674730	
10			Seitz, Mihel	US 6706634	2004.0	7	Control of separation between transfer gate	438/692	257/E21.65		✓							US 670663	

Ready   NUM